TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

TA6009FN, TA6009FNG

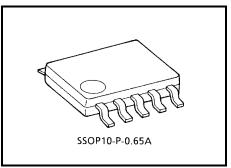
Shock Sensor IC (1 ch version)

TA6009FN/FNG detects an existence of external shock through the shock sensor and output.

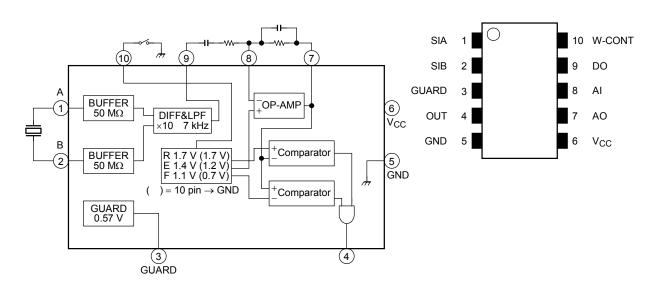
Features

- TA6009FN/FNG operates from 2.7 to 5.5 V DC single power supply voltage.
- Signal from the shock sensor is amplified according to setting gain, and is detected through the internal window comparator.
- TA6009FN/FNG incorporates 1-ch shock detecting circuitry.
- Input terminal of sensor signal is designed high impedance. Differential input impedance = $100 \text{ M}\Omega$ (typ.)
- LPF (low pass filter) circuitry is incorporated. Cut-off frequency of LPF = 7 kHz
- Sensitivity of shock detection can be adjusted by external devices.
- Small package SSOP10-P-0.65A (0.65 mm pitch)

Block Diagram



Weight: 0.04 g (typ.)



Pin Connection (top view)

Pin Function

Pin No.	Pin Name	Function
1	SIA	Connection terminal of shock sensor
2	SIB	Connection terminal of shock sensor
3	GUARD	Input (1, 2 pin) GUARD terminal
4	OUT	Output terminal (output = "L" when shock is detected.)
5	GND	Ground terminal
6	V _{CC}	Power supply voltage
7	AO	Op-Amp output terminal
8	AI	Op-Amp input terminal
9	DO	Differential-Amp output terminal
10	W-CONT	WindComp. trip voltage selection terminal

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	7	V
Power dissipation	PD	300	mW
Storage temperature	T _{stg}	-55 to 150	°C

Recommend Operating Condition

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	2.7 to 5.5	V
Operating temperature	T _{opr}	-25 to 85	°C

Electrical Characteristics (unless otherwise specified, $V_{CC} = 3.3 V$, Ta = 25°C)

Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Supply voltage	V _{CC}	_	—	2.7	3.3	5.5	V
Current	1	(1)	V _{CC} = 3.3 V		1.8	2.4	m (
Supply current	ICC		$V_{CC} = 5.0 V$		1.8	2.4	mA

(GUARD)

Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Output voltage	VoGur	(2)	—	0.52	0.57	0.62	V

(DIFF-AMP)

Characteristics		Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Input impedance	(Note 1)	Zin	_	—	50	100		MΩ
Gain		GvBuf	(3)	—	19.6	20	20.4	dB
Output DC voltage		VoBuf	(4)	Connect C = 100 pF between 1 pin and 2 pin	0.7	1	1.3	V
Low pass filter cut-off freq.		fc	(5)	Frequency at –3dB point	5	7	10	kHz
Output source current		IBso	(6)	$Voh = V_{CC} - 1 V$	400	800		μA
Output sink current		IBsi	(7)	Vol = 0.3 V	75	130		μA

Note 1: Marked parameters are reference data.

(OP-AMP)

Characteristics		Symbol	Test Circuit	Test Condition		Min	Тур.	Max	Unit
Cut-off frequency	(Note 1)	fT	_	_		1.5	2		MHz
Openloop gain	(Note 1)	Gvo	_	_		80	90		dB
Input voltage 1		Vin1	(8)	10 pin \rightarrow OPEN	(Note 2)	1.33	1.4	1.47	V
Input voltage 2		Vin2	(9)	10 pin \rightarrow GND	(Note 2)	1.14	1.2	1.26	V
Input current		l _{in}	(10)	—			25	50	nA
Offset voltage	(Note 1)	Voff	_	_		-5	0	5	mV
Output source current		IAso	(11)	$Voh = V_{CC} - 1 V$		300	800		μA
Output sink current		IAsi	(12)	Vol = 0.3 V		130	200		μA

Note 1: Marked parameters are reference data.

Note 2: 10 pin must be non-connected otherwise connected to GND.

(window-comparator)

Characteristics		Symbol	Test Circuit	Test Condition		Min	Тур.	Max	Unit
Trip voltage 1	(Note 1)	Vtrp1	_	10 pin \rightarrow OPEN (No	te 2)	Vin1 ±0.285	Vin1 ±0.3	Vin1 ±0.315	V
Trip voltage 2	(Note 1)	Vtrp2	_	10 pin \rightarrow GND (No	te 2)	Vin2 ±0.475	Vin2 ±0.5	Vin2 ±0.525	V
Output source current		IWso	(13)	$Voh = V_{CC} - 0.5 V$		30	50		μA
Output sink current		IWsi	(14)	Vol = 0.3 V		300	800		μA

Note 1: Marked parameters are reference data.

Note 2: 10 pin must be non-connected otherwise connected to GND.

Application Note

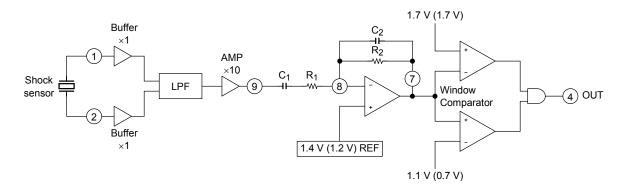


Figure 1 The Composition of G-Force Sense Amplifier

Figure 1 is the composition of G-Force sense amplifier.

The shock sensor is connected between $1\ {\rm and}\ 2\ {\rm terminal}.$

When G-force Sensor (sensor sensibility = s (mV/G)) is used to detect external shock of g (G), the external parts are determined as following.

 $\begin{array}{l} (\text{gain setting})*10 \; \text{PIN} \rightarrow \text{GND} \\ 500/(\text{s}\times\text{g}) = \text{G1} \\ \text{G1/10} = \text{G} \; (\text{OP-AMP}) \end{array}$

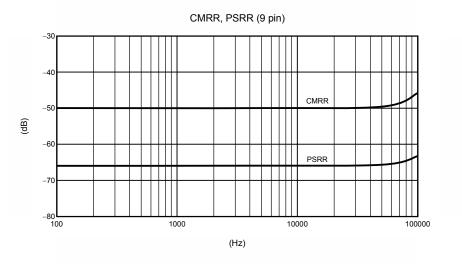
(HPF setting) $\label{eq:constraint} \begin{array}{l} \mbox{(HPF setting)} \\ \mbox{fc} = 1/(2 \ \pi \times R_1 \times C_1) \end{array}$

(LPF setting) fc = $1/(2 \pi \times R_2 \times C_2)$

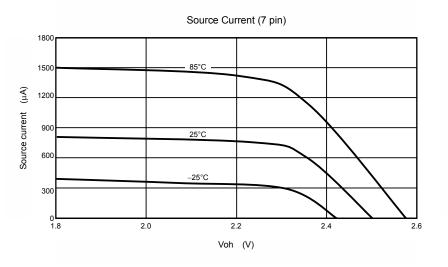
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Reference Data

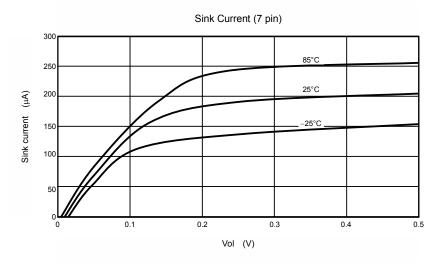
(1) 9 pin (DIFF-AMP output) CMRR, PSRR



(2) 7 pin (OP-AMP output) source current

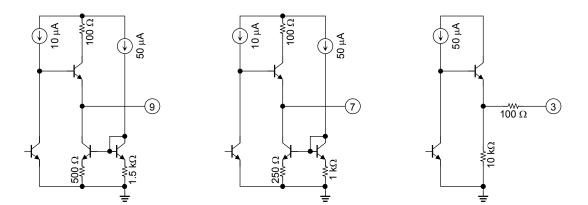


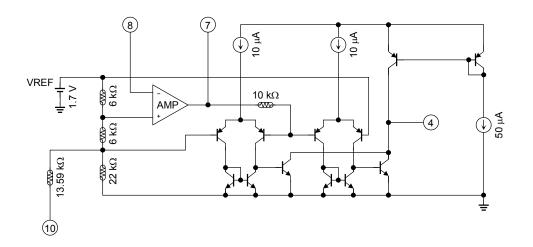
(3) 7 pin (OP-AMP output) sink current



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Equivalent Circuit

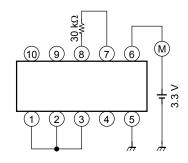




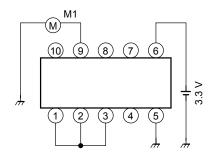
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Test Circuit

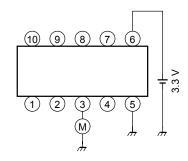
(1) Supply current **ICC**



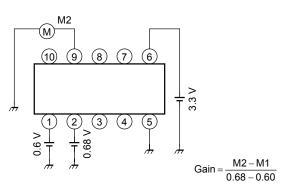
(3) DIFF-AMPGain GvBufStep 1



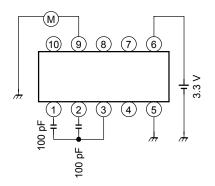
(2) GUARD Output voltage **VoGur**



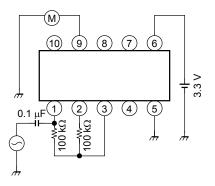




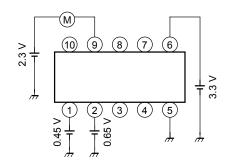
(4) DIFF-AMP Output DC voltage **VoBuf**



(5) DIFF-AMP Low pass filter cut-off freq. **fc**

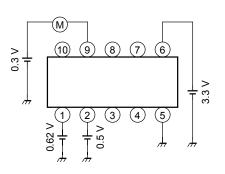


(6) DIFF-AMP Output source current **IBso**

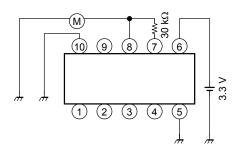


- (8) OP-AMPInput voltage 1 Vin1

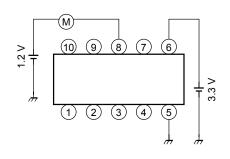
(7) DIFF-AMP Output sink current **IBsi**



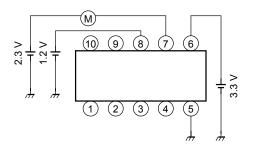
(9) OP-AMP Input voltage 2 **Vin2**



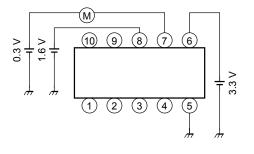
(10) OP-AMP Input current **I**in



(11) OP-AMP Output source current **IAso**

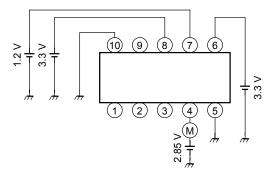


(12) OP-AMP Output sink current **IAsi**

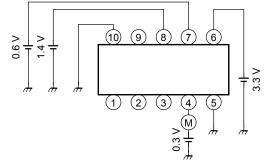




(13) Window comparator Output source current **IWso**

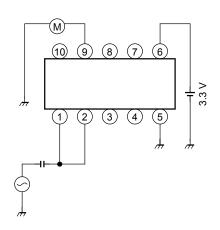


(14) Window comparatorOutput sink current **IWsi**

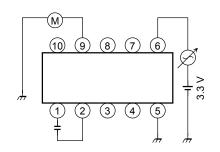


Test Circuit (for reference)

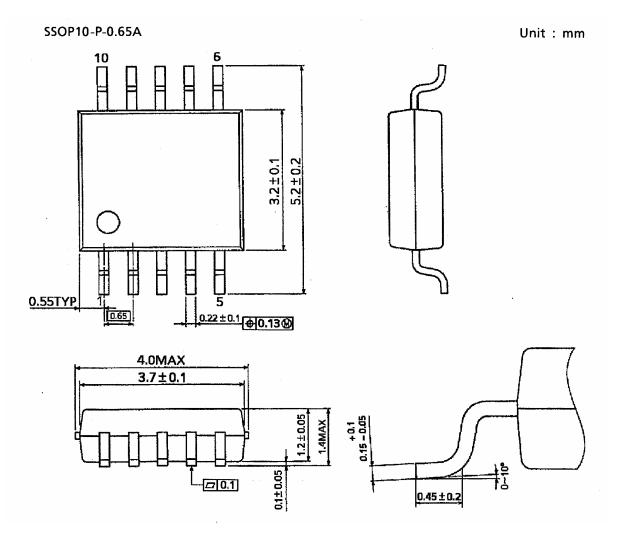




(b) DIFF-AMP **PSRR**



Package Dimensions



Weight: 0.04 g (typ.)

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